

Amplifier, Power, 1.2W 5.7-8.5 GHz

MAAP-000068-PKG003

Rev —
Advance Datasheet

Features

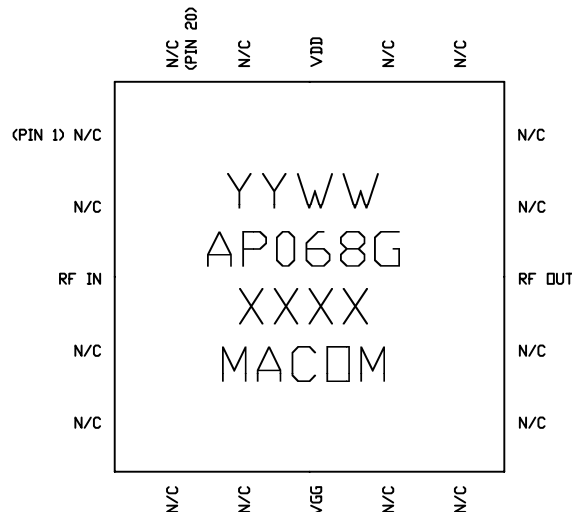
- ◆ **1.2 Watt Saturated Output Power Level**
- ◆ **Variable Drain Voltage (4-10V) Operation**
- ◆ **MSAG™ Process**

Description

The MAAP-000068-PKG003 is a 3-stage 1.2 W power amplifier with on-chip bias networks in a 20 lead, 5 mm PQFN package, allowing easy assembly. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Each device is 100% RF tested to ensure performance compliance. The part is fabricated using M/A-COM's GaAs Multifunction Self-Aligned Gate (MSAG) Process.

The 5 mm PQFN package has a lead-free lead finish that is RoHS compliant and compatible with a 260°C reflow temperature. The package also features low lead inductance and an excellent thermal path. The MTTF is 1,000,000 hours at 170°C.



Primary Applications

- ◆ **Point-to-Point Radio**
 - ◇ **6, 7, and 8 GHz Bands**
- ◆ **SatCom**
- ◆ **Broadband Wireless Access**

Electrical Characteristics: $T_C = 35^\circ\text{C}^1$, $Z_0 = 50\ \Omega$, $V_{DD} = 8\text{V}$, $I_{DQ} = 320\text{mA}^2$, $P_{in} = 8\text{dBm}$, $R_G = 60\Omega$

Parameter	Symbol	Typical	Units
Bandwidth	f	5.7-8.5	GHz
Output Power	P_{OUT}	31	dBm
1-dB Compression Point	P_{1dB}	30	dBm
Small Signal Gain	G	25	dB
Input VSWR	VSWR	1.6:1	
Output VSWR	VSWR	2.5:1	
Output Third Order Intercept	TOI	38	dBm
Output Third Order Intermod, $P_{out} = 24\text{ dBm (DCL)}$	IMD3	35	dBc
Gate Current	I_{GG}	5	mA
Drain Current	I_{DD}	470	mA

1. T_C = Case Temperature
2. Adjust V_{GG} between -2.6 and -1.2V to achieve specified I_{DQ} .

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Maximum Operating Conditions ³

Parameter	Symbol	Absolute Maximum	Units
Input Power	P_{IN}	13.0	dBm
Drain Supply Voltage	V_{DD}	+12.0	V
Gate Supply Voltage	V_{GG}	-3.0	V
Quiescent Drain Current (No RF)	I_{DQ}	520	mA
Quiescent DC Power Dissipated (No RF)	P_{DISS}	5.2	W
Junction Temperature	T_J	170	°C
Storage Temperature	T_{STG}	-55 to +150	°C

3. Operation beyond these limits may result in permanent damage to the part.

Recommended Operating Conditions ⁴

Characteristic	Symbol	Min	Typ	Max	Unit
Drain Voltage	V_{DD}	4.0	8.0	8.0	V
Gate Voltage	V_{GG}	-2.6	-2.0	-1.2	V
Input Power	P_{IN}		8.0	11.0	dBm
Thermal Resistance	Θ_{JC}		32		°C/W
Case Temperature	T_C			Note 4	°C

4. Operation outside of these ranges may reduce product reliability.

5. Case Temperature = 170°C — $\Theta_{JC} * V_{DD} * I_{DQ}$

Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply $V_{GG} = -2$ V, $V_{DD} = 0$ V.
2. Ramp V_{DD} to desired voltage, typically 8.0 V.
3. Adjust V_{GG} to set I_{DQ} , (approximately @ -2 V).
4. Set RF input.
5. Power down sequence in reverse. Turn V_{GG} off last.



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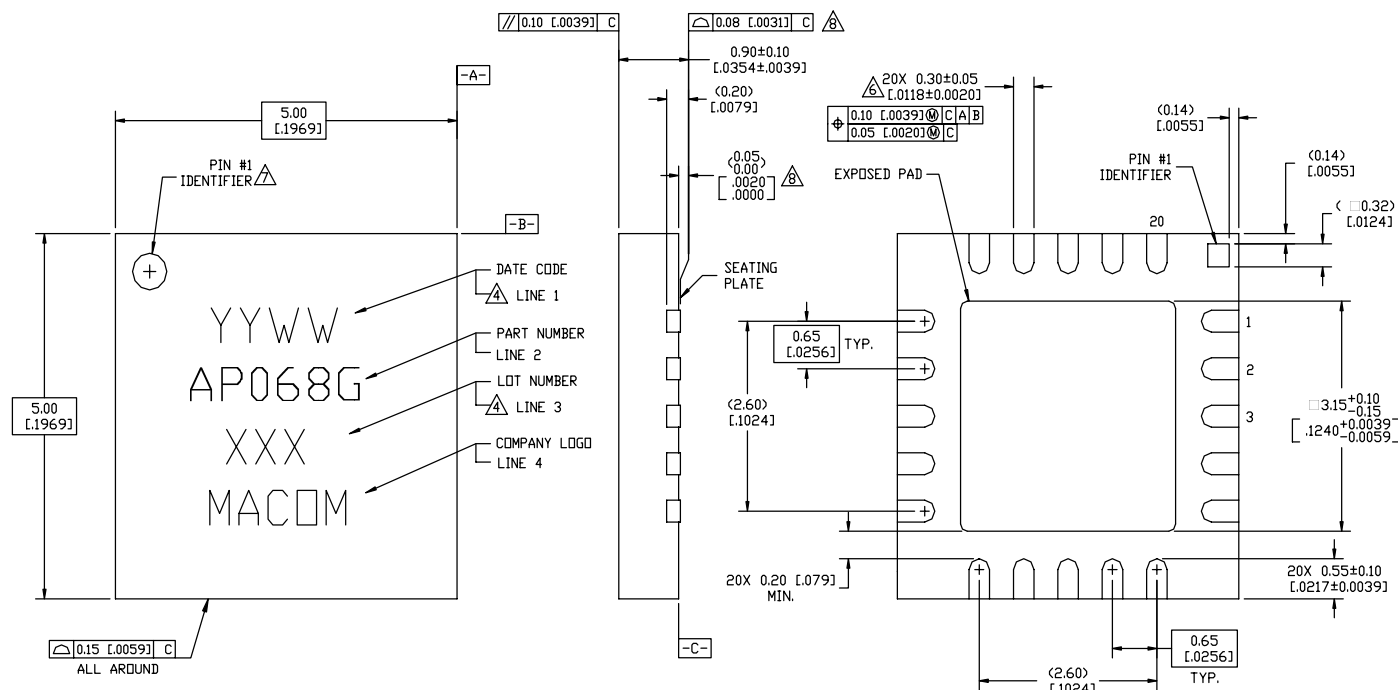


Figure 1. 5x5 mm 20-Lead MLP.

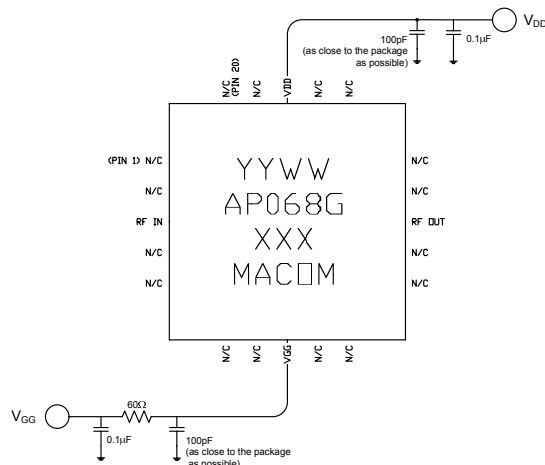


Figure 2. Recommended Bias Configuration.

Note: The exposed pad centered on the package bottom must be connected to RF and dc ground for proper electrical and thermal operation.

Refer to M/A-COM Application Note **Surface Mounting Instructions for PQFN Packages #S2083*** for assembly guidelines.

Additional Precaution: All parts must receive a bake-out of 125°C for 24 hours prior to any solder reflow operation.

*Application Notes can be found by going to the Site Search Page of M/A-COM's web page (<http://www.macom.com/Application%20Notes/index.htm>) and searching for the required Application Note.

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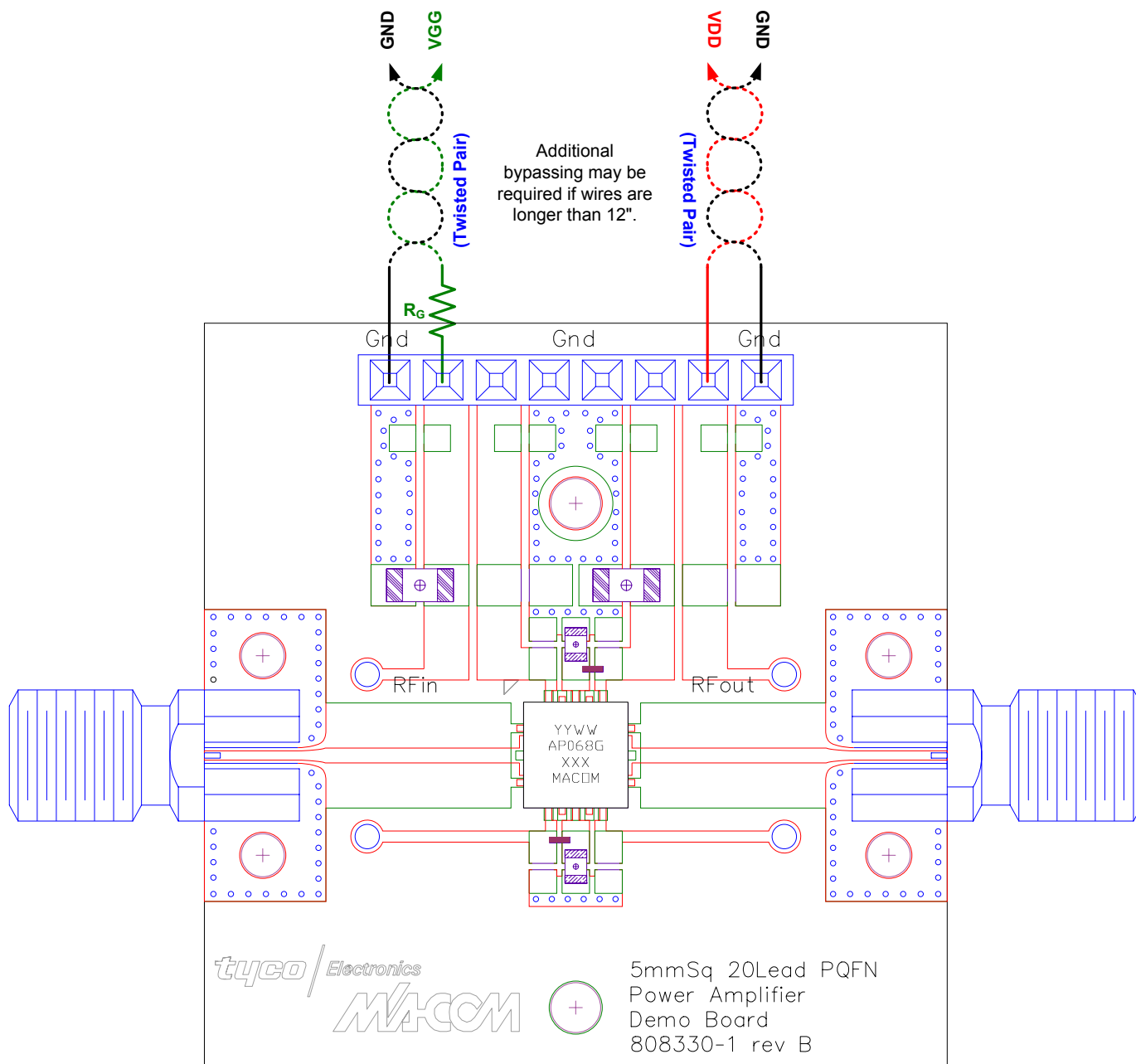


Figure 3. Demonstration Board P/N MAAP-000068-SMB003 (available upon request).